

Memory

Read-Only Memories

- **Mask ROM**
 - Programmed permanently during manufacturing process
- **Programmable ROM**
 - **PROM**
 - programmed by fusing or anti-fusing process
 - the process is irreversible
 - **Erasable PROM**
 - **UV EPROM**
 - **EEPROM**

Random Access Memories

- **Transistor efficient methods for implementing storage elements**
- **Small RAM: 256 words by 4-bit**
- **Large RAM: 1 billion words by 1-bit**
- **Static RAMs and Dynamic RAMs**

Static RAMs

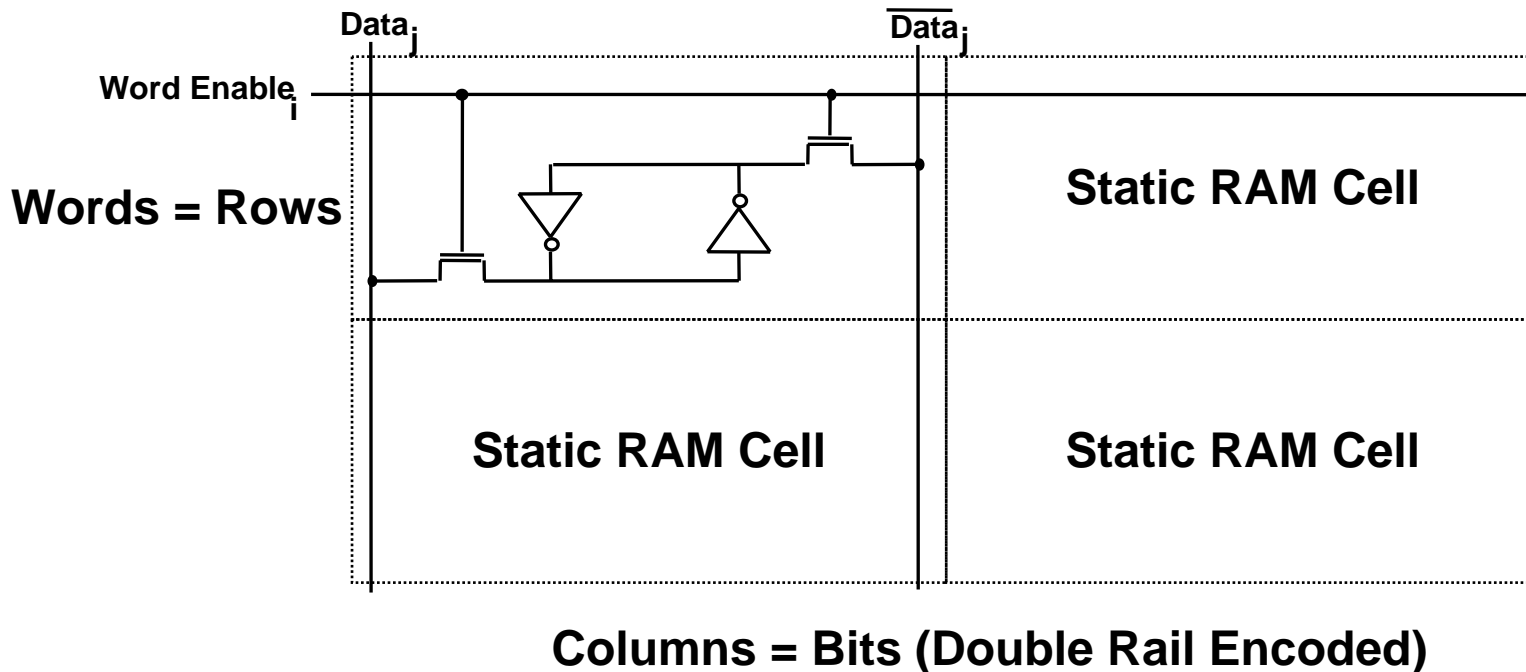
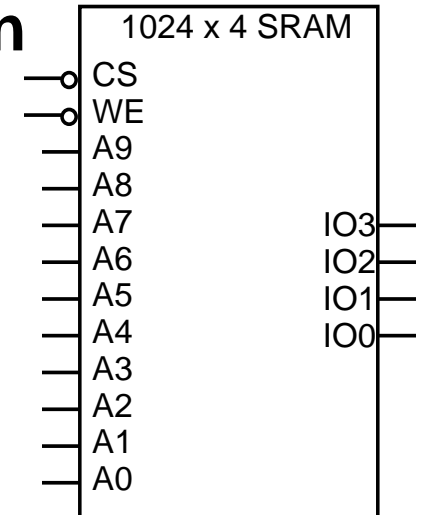
- We will discuss a 1024 x 4 organization

Chip Select Line (active lo)

Write Enable Line (active lo)

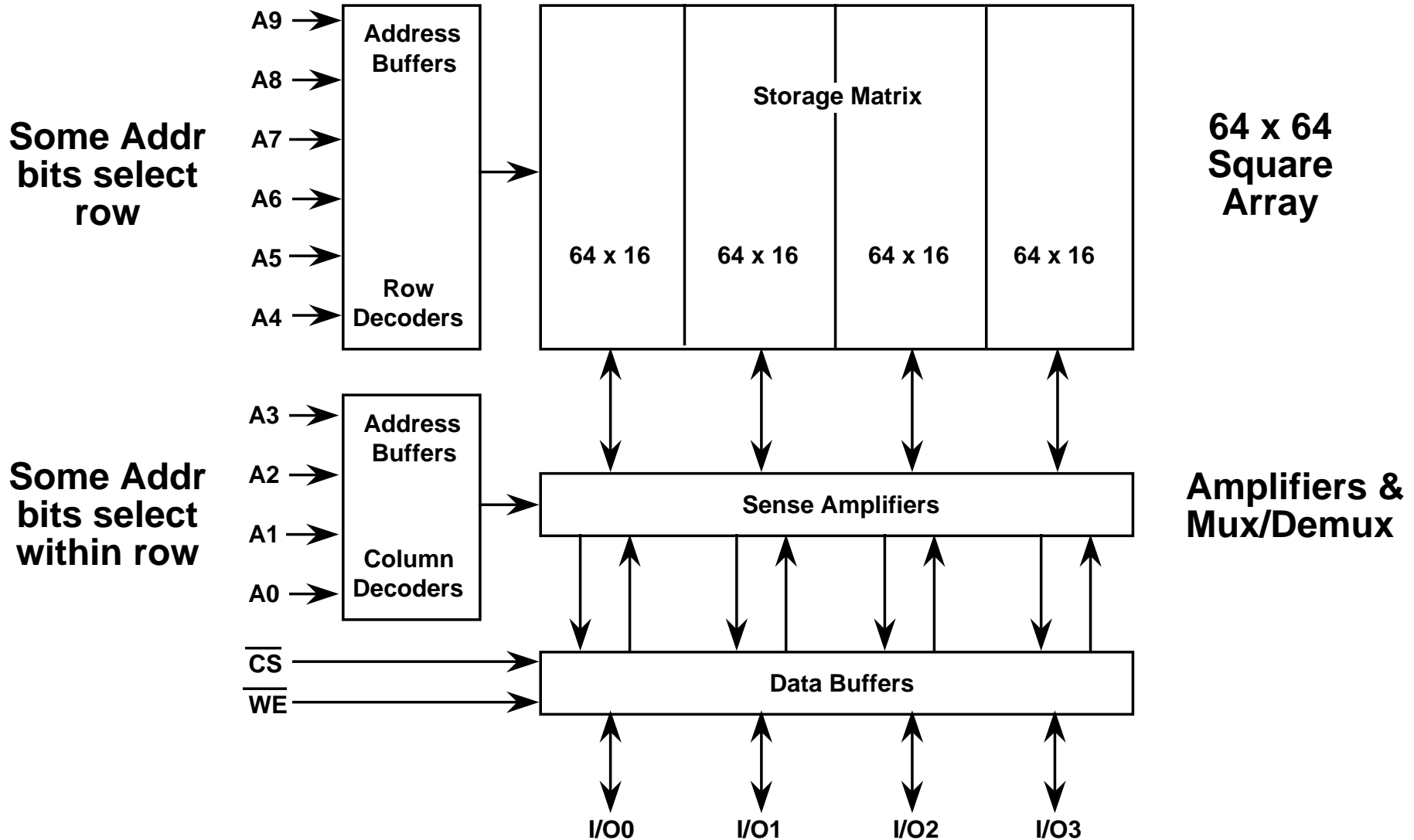
10 Address Lines

4 Bidirectional Data Lines



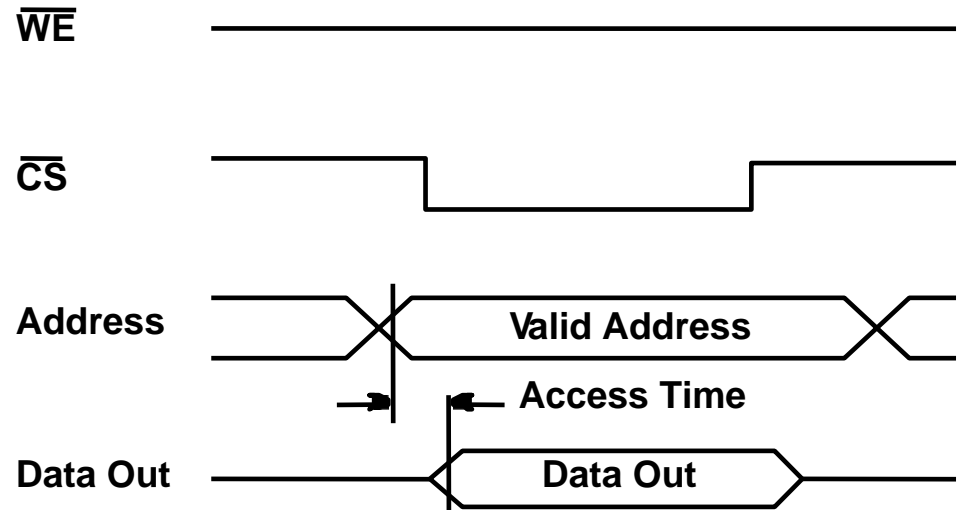
RAM Organization

Long thin layouts are not the best organization for a RAM

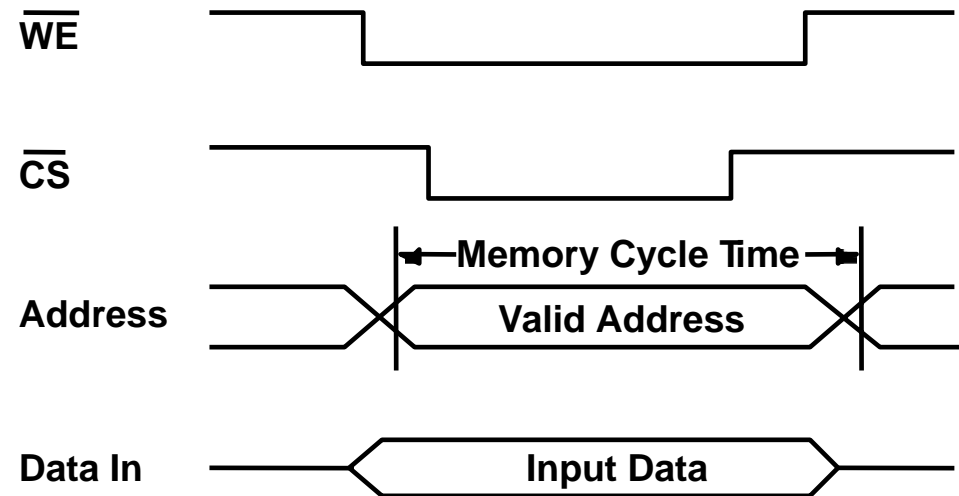


RAM Timing

Simplified Read Timing



Simplified Write Timing



Dynamic RAMs

1 Transistor (+ capacitor) memory element

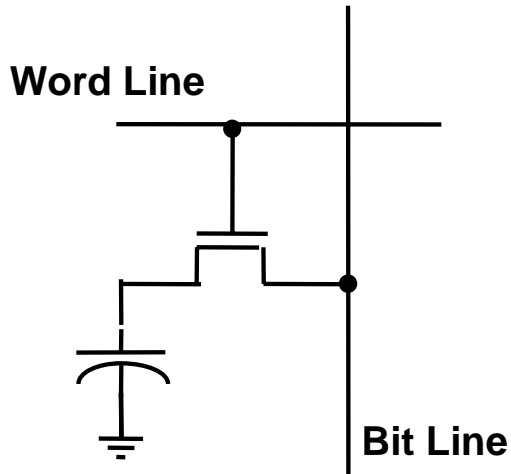
Read: Assert Word Line, Sense Bit Line

Write: Drive Bit Line, Assert Word Line

Need for Refresh Cycles: storage decay in ms

Destructive Read-Out

Internal circuits read word and write back



DRAM Organization

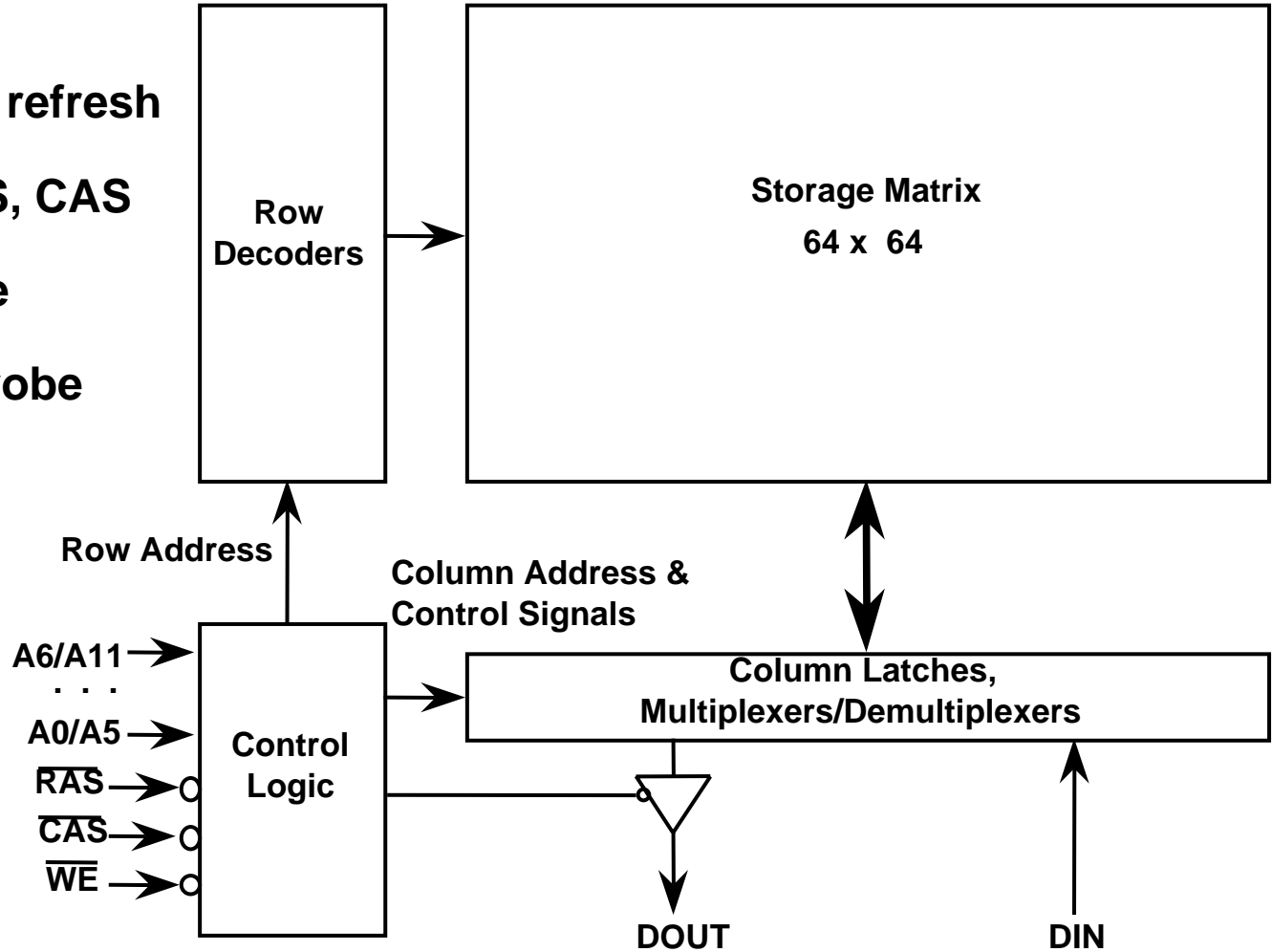
Long rows to simplify refresh

Two new signals: RAS, CAS

Row Address Strobe

Column Address Strobe

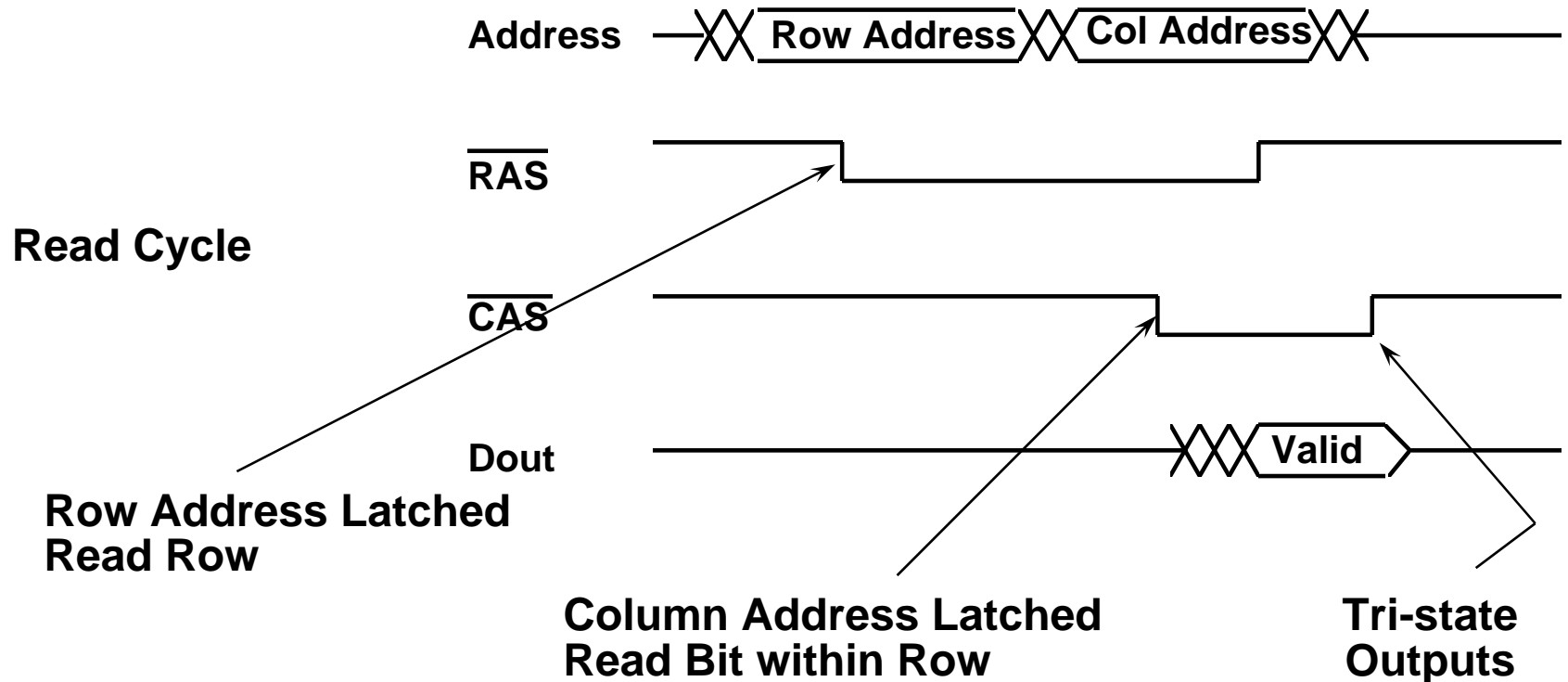
Replace Chip Select



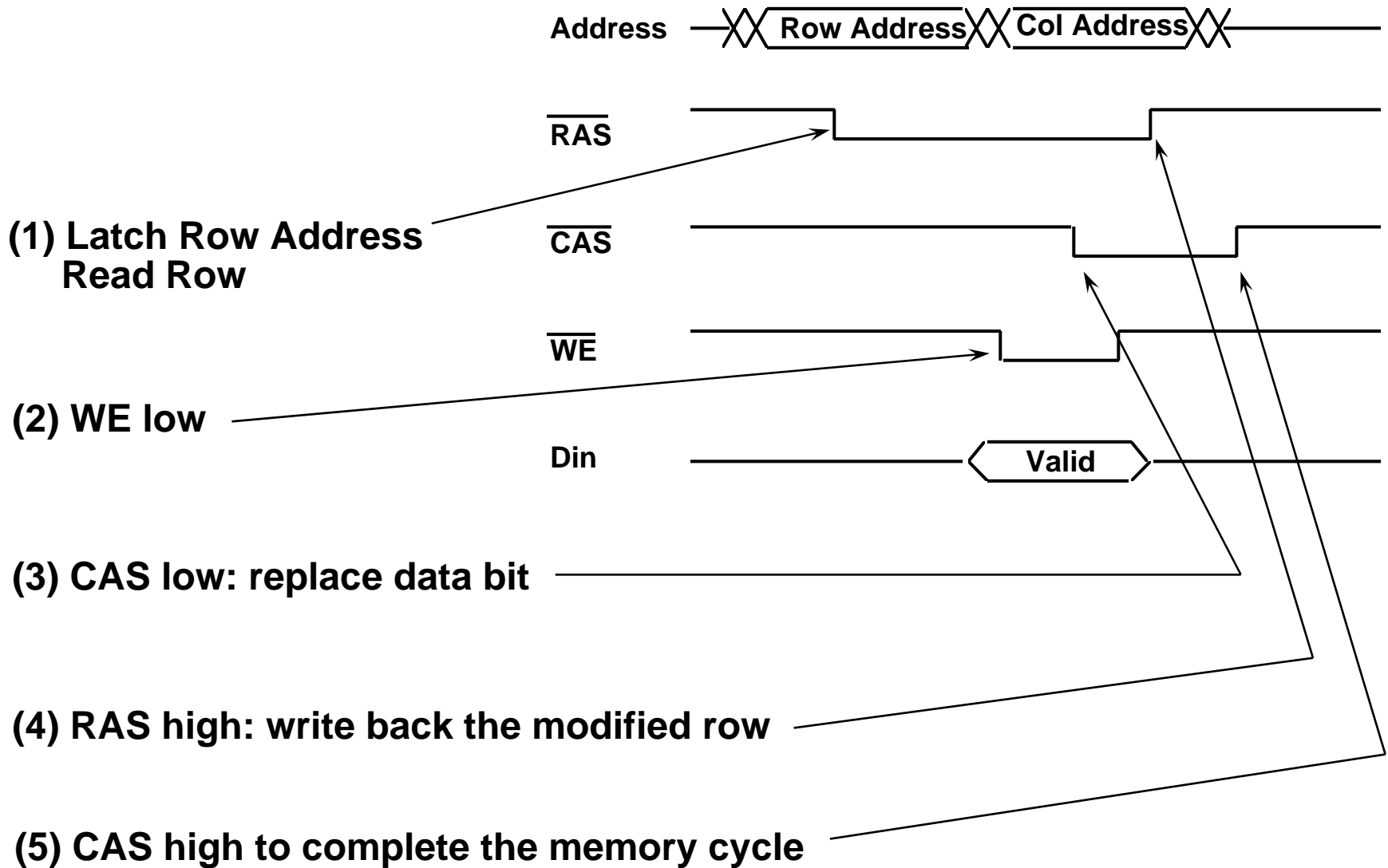
RAS, CAS Addressing

Even to read 1 bit, an entire 64-bit row is read!

Separate addressing into two cycles: Row Address, Column Address
Saves on package pins, speeds RAM access for sequential bits!



Write Cycle Timing



RAM Refresh

Refresh Frequency:

**4096 word RAM -- refresh each word once every 4 ms
=> This is one refresh cycle every 976 ns**

**Assume 120ns memory access cycle
=> 1 in 8 DRAM accesses!**

**But RAM is really organized into 64 rows
=> This is one refresh cycle every 62.5 μ s (1 in 500 DRAM accesses)**

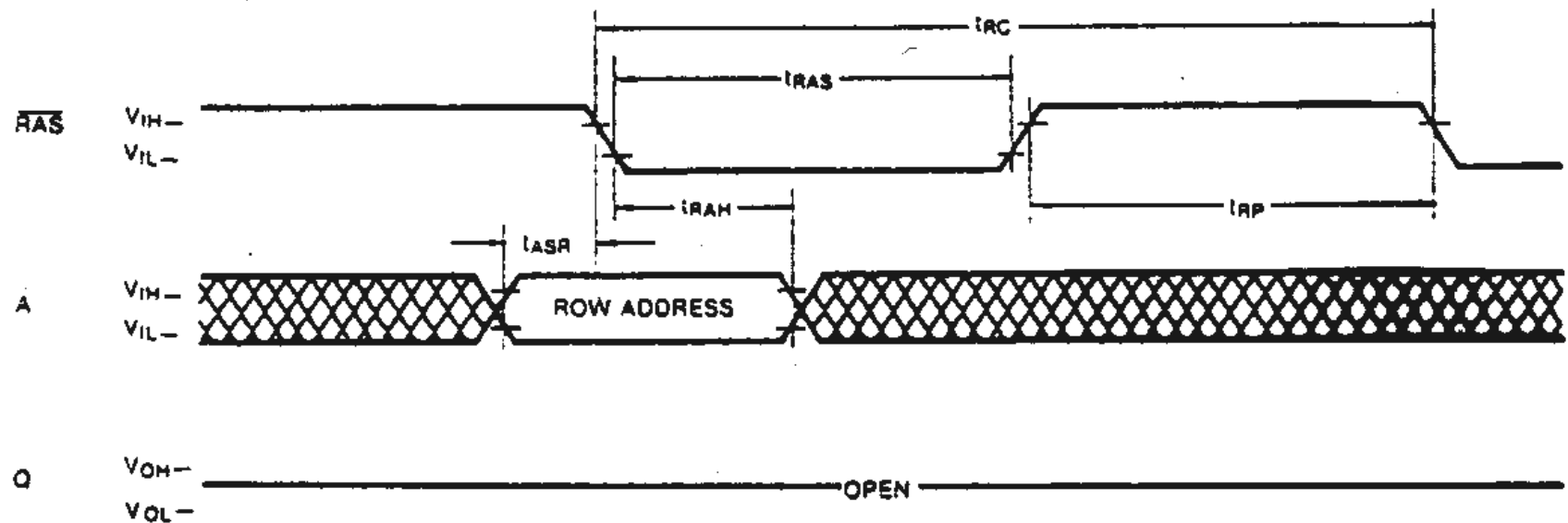
Large capacity DRAMs have 256 rows, refresh once every 16 μ s

RAS-only Refresh (RAS cycling, no CAS cycling)

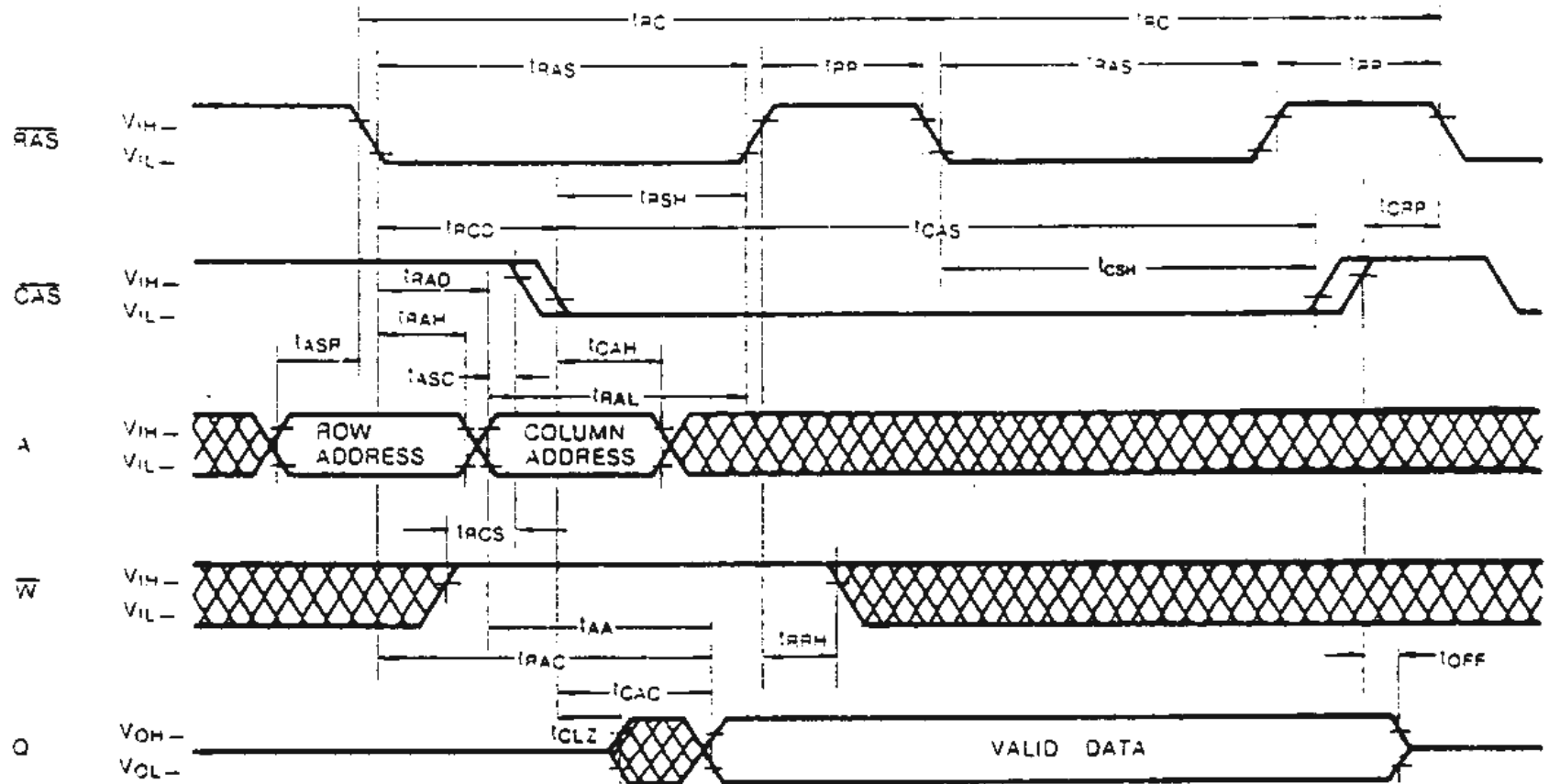
External controller remembers last refreshed row

Some memory chips maintain refresh row pointer

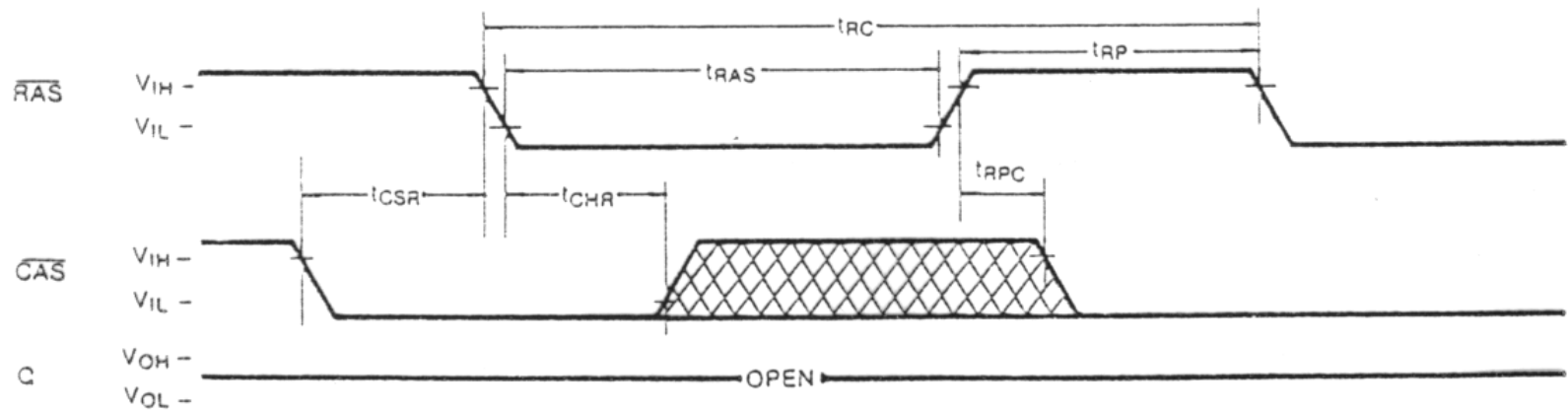
CAS before RAS refresh: if CAS goes low before RAS, then refresh

RAS-ONLY REFRESH CYCLENote: $\overline{\text{CAS}} = V_{IH}$, $\overline{\text{W.D.}}, A_9 = \text{Don't Care}$ 

HIDDEN REFRESH CYCLE



$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE



 DON'T CARE

- **DRAM Variations**

Page Mode DRAM:

read/write bit within last accessed row without RAS cycle

RAS, CAS, CAS, . . ., CAS, RAS, CAS, ...

New column address for each CAS cycle

Static Column DRAM:

like page mode, except address bit changes signal new cycles rather than CAS cycling

on writes, deselect chip or CAS while address lines are changing

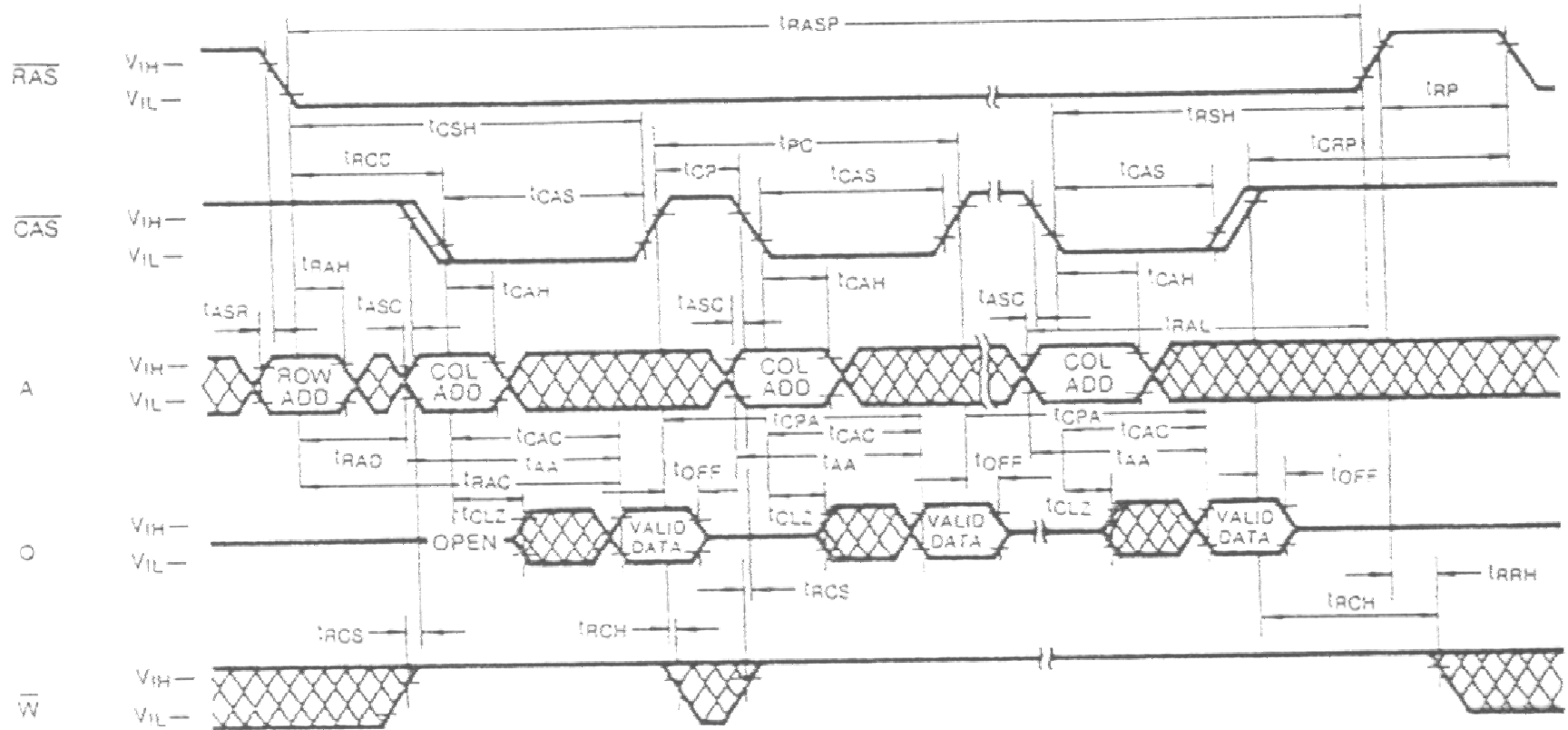
Nibble Mode DRAM:

like page mode, except that CAS cycling implies next column address in sequence -- no need to specify column address after first CAS

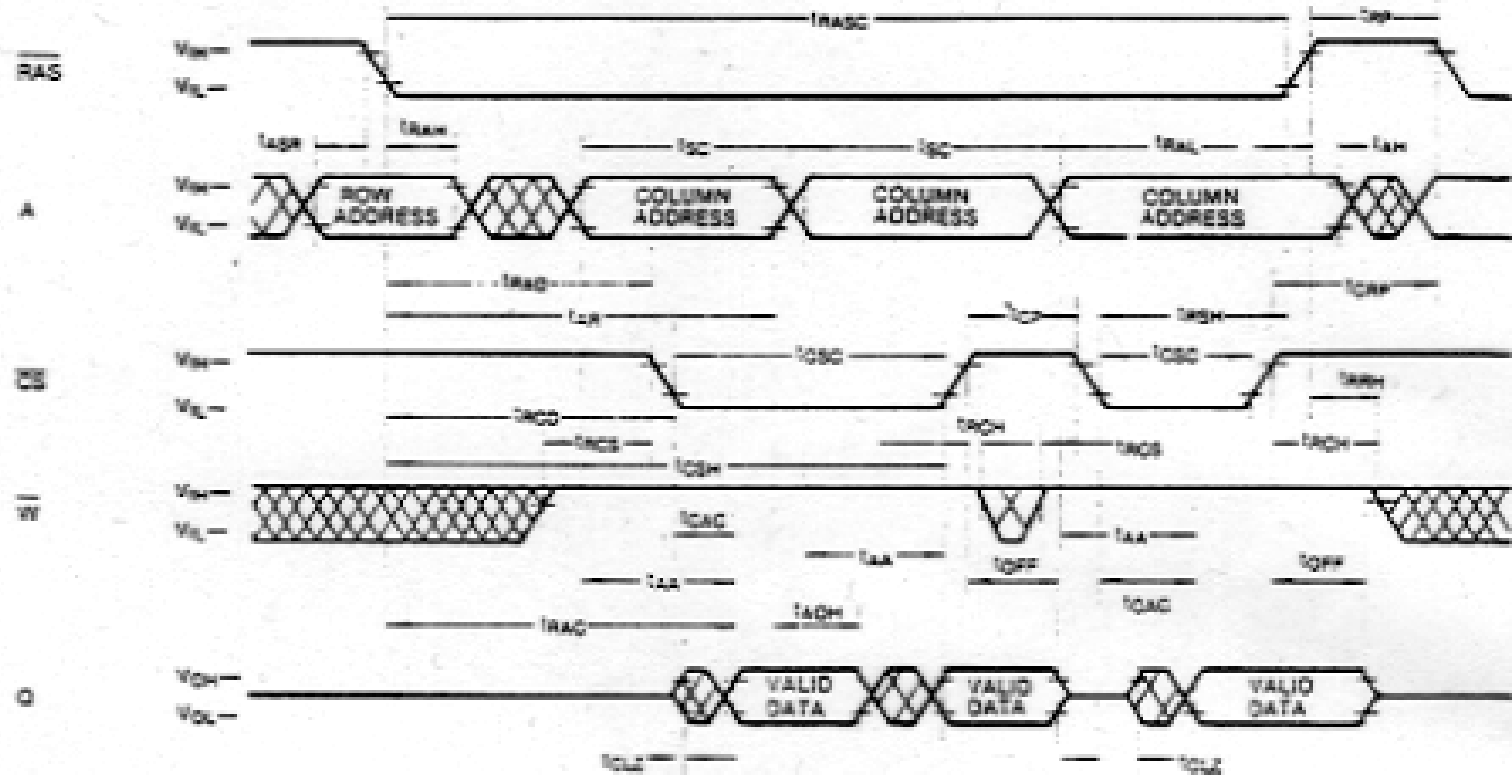
Works for 4 bits at a time (hence "nibble")

RAS, CAS, CAS, CAS, CAS, RAS, CAS, CAS, CAS, CAS, . . .

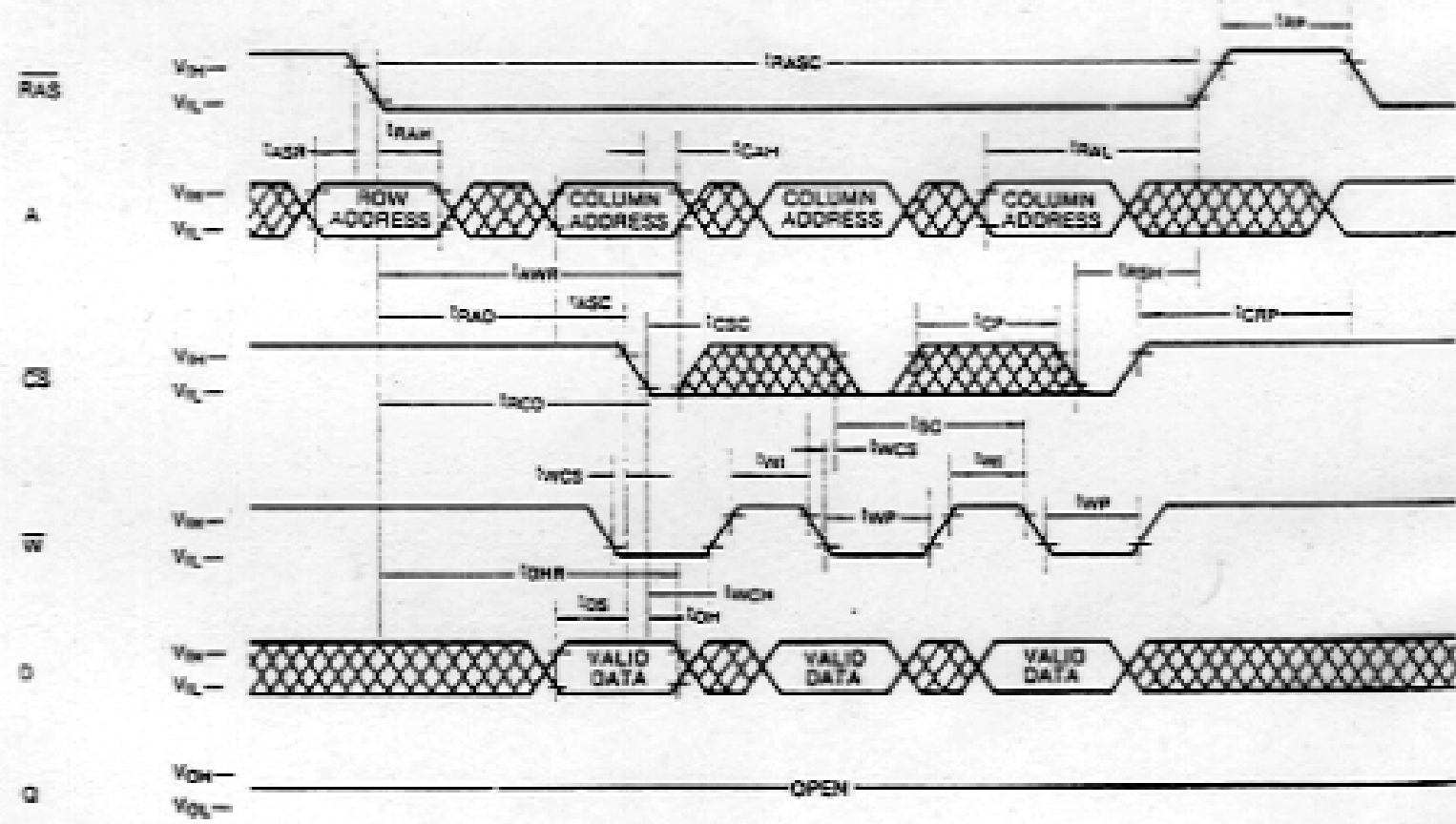
FAST PAGE MODE READ CYCLE



STATIC COLUMN MODE READ CYCLE



STATIC COLUMN MODE WRITE CYCLE (\overline{W} controlled early write)



- **More advanced DRAM Technologies**
 - **EDO DRAM (Extended Data Out DRAM)**
 - One access to the memory can begin before the last one has finished
 - **SDRAM (Synchronous DRAM)**
 - Tied to the system clock and is designed to be able to read or write memory in burst mode (after the initial read or write latency) at 1 clock cycle per access (zero wait states)
 - **DDR SDRAM (Double Data Rate SDRAM)**
 - Doubles the bandwidth of the memory by transferring data twice per cycle on both the rising and falling edges of the clock signal
 - **DRDRAM (Direct Rambus DRAM)**
 - **SLDRAM (Synchronous-Link DRAM)**